

Claim Sheet – Preliminary Amendment

Docket 261/136

91. A method for cleaning a semiconductor article, comprising the steps of:
contacting the article with an oxidizing solution;
rinsing the article; and
exposing the article to a vapor comprising ozone.
92. A method for cleaning a surface of a semiconductor article, comprising the steps of:
loading the semiconductor article into a chamber;
providing a heated liquid solution onto the surface of the article within the chamber, the solution including deionized water;
providing ozone into the chamber; and
rotating the article within the chamber with the heated liquid solution on the surface of the article.
93. The method of claim 92 where the solution is heated to a temperature between room temperature and 100°C.
94. The method of claim 92 where the solution is heated to a temperature between 50-90°C.
95. The method of claim 92 where the article is rotated at 200-2000rpm.
96. The method of claim 91 with the liquid further including hydrogen flouride.

